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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Applicant Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Gu, Shuo
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 1

Attorney Docket No: MA-108

US PATENT DOCUMENTS

Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
GP	A1	5,821,152	10/13/1998	Han et al.			
GP	A2	5,923,968	07/13/1999	Yamazaki et al.			
GP	A3	6,146,966	11/14/2000	Hirota et al.			
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FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
GP	A6	BANERJEE, ADITI., et al. , "Fabrication and Performance of Selective HSG Storage Cells for 256 Mb and 1Gb DRAM Applications", <u>IEEE Transactions on Electron Devices</u> , Vol.47, No.3, (3/2000),584-592	
GP	A7	BO, XIANG-ZHENG., et al. , "Spatially selective single-grain silicon films induced by hydrogen plasma seeding", <u>J. Vac. Sci. Technol. B</u> 20(3), (May/Jun 2002),	
GP	A8	DAHLHEIMER, C..E. , et al. , "Laser-Interference Crystallization of Amorphous Silicon", 54-55	
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EXAMINER

DATE CONSIDERED

9/3/05

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached